High-Performance CMOS Two Channel 4PST Switch

FEATURES

- Low on-resistance: $r_{DS(on)} = 5\Omega$
- Wide bandwidth: 1.3GHz (-3dB point)
- Crosstalk: –100dB @ 50KHz, –70dB @ 5MHz, –50dB @ 30MHz
- Off-isolation: –90dB @ 50KHz, –60dB @ 5MHz, –55dB @ 30MHz,
- Single 5V supply
- Bidirectional signal flow
- TTL compatible control inputs
- Ultra-low quiescent current: 3µA
- Switch turn on time of 6.5ns

APPLICATIONS

- High-speed video signal switching/routing
- HDTV-quality video signal routing
- Audio signal switching/routing
- Data acquisition
- ATE systems
- Telecomm routing
- Token Ring transceivers
- High-speed networking

GENERAL DESCRIPTION

The QS4A105Q is a high-performance CMOS Two-Channel 4PST switch with 3-state outputs. The low on-resistance of the QS4A105Q allows inputs to be connected to outputs with low insertion loss and high bandwidth.

The QS4A105Q with 1.3GHz bandwidth, makes it ideal for high-performance video signal switching, audio signal switching, and telecomm routing applications. Low power dissipation makes this device ideal for battery operated and remote instrumentation applications.

The QS4A105Q is offered in the QSOP package which has several advantages over conventional packages such as PDIP and SOIC including:

- Reduced signal delays due to denser component packaging on circuit boards
- Reduced system noise due to less pin inductance

Figure 1. Functional Block Diagram

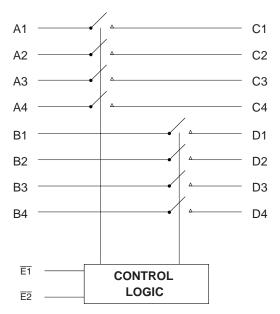


Figure 2. Pin Configuration

(All Pins Top View)

	QSOP	
E1 C 1 A1 C 2 D4 C 3 A2 C 4 D3 C 5	20 19 18 17 16	□ V _{CC} □ E2 □ C1 □ B4 □ C2
A3 G D2 7 A4 8 D1 9 GND 10	10 15 14 13 12 11	B3 C3 B2 C4 B1

Table 1. Pin Definitions

Name	I/O	Description
<u>E1</u> , <u>E2</u>	Ι	Enable
A _N , B _N	I/O	Port A, Port B
C _N , D _N	I/O	Port C, Port D

Table 2. Function Table

Table 2.	Function	Table	any	
E1	E2	A _N , C _N I/Os	B _N , D _N I/Os	m Da.
Н	Н	Disconnected	Disconnected	
L	Н	$A_N = C_N$	Disconnected	
Н	L	Disconnected	$B_N = D_N$	TM
L	L	$A_N = C_N$	$B_N = D_N$	

Table 3. Absolute Maximum Ratings

Supply Voltage to Ground	–0.5V to +7.0V
DC Switch Voltage V _S	
Analog Input Voltage	
DC Input Voltage V _{IN}	
AC Input Voltage (for a pulse width ≤ 20ns)	
DC Output Current Max. Sink Current/Pin	120mA
Maximum Power Dissipation	0.7 watts
T _{STG} Storage Temperature	–65° to +150°C

Note: ABSOLUTE MAXIMUM RATINGS are those conditions beyond which damage to the device may occur. Exposure to these conditions or beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rating conditions is not implied.

Table 4. Power Supply Characteristics

Symbol	Parameter	Test Conditions	Max	Unit
I _{CC}	Supply Current	V_{CC} = Max., V_{IN} = GND or V_{CC}	3	μΑ

Table 5. Electrical Characteristics Over Operating Range

Commercial: $T_A = 0^{\circ}C$ to $70^{\circ}C$, $V_{CC} = 5.0V \pm 5\%$

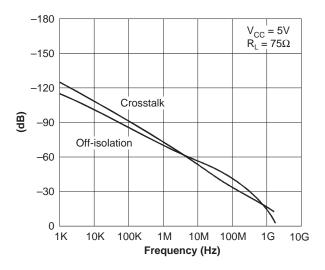
Symbol	Parameter	Test Conditions	Min	Typ ⁽¹⁾	Max	Unit		
Analog S	Analog Switch							
V _{IN}	Analog Signal Range ⁽²⁾		0		V _{CC} -1	V		
r _{DS(on)}	Drain-source On-resistance ^(2,3)	V_{CC} = Min., V_{IN} = 0.0V, I_{ON} = 30mA		5	7	Ω		
		$V_{CC} = Min., V_{IN} = 1.5V,$	—	5.5	8	Ω		
$\Delta r_{\text{DS(on)}}$	r _{DS(on)} Matching Between Channels ^(2,3,4)	V_{CC} = Min., V_{IN} = 0.0V, I_{ON} = 30mA	_	1	4	Ω		
		V_{CC} = Min., V_{IN} = 1.5V, I_{ON} = 15mA		1	_	Ω		
I _{C (OFF)}	Channel Off Leakage Current	$ \begin{array}{l} A_{N},B_{N}=V_{CC}\text{or}0V,\\ C_{N},D_{N}=0V\text{or}V_{CC},\overline{E}=V_{CC} \end{array} $		1	_	nA		
I _{C (ON)}	Channel On Leakage Current	$A_N = B_N = C_N = D_N = 0V$, Each Channel is Turned On Sequentially		1	_	nA		
Digital C	ontrol			-2				
V _{IH}	Input HIGH Voltage	Guaranteed Logic HIGH for Control Pins	2.0	9	_	<		
V _{IL}	Input LOW Voltage	Guaranteed Logic LOW for Control Pins	_		0.8	V		
Dynamic	Characteristics							
$t_{ON(\overline{E})}$	Enable Turn-on Time \overline{E} to A_N , B_N , C_N or D_N	$R_L = 1K\Omega, C_L = 100pF$ (See Figure 9)	0.5	—	6.5	ns		
$t_{OFF(\overline{E})}$	Enable Turn-off Time \overline{E} to A_N , B_N , C_N or D_N	$R_L = 1K\Omega$, $C_L = 100pF$ (See Figure 9)	0.5	—	6.0	ns		
t _{PD}	Group Delay ^(2,5)	$R_L = 1K\Omega, C_L = 100pF$	—	—	250	ps		
f _{3dB}	–3 dB Bandwidth	V_{IN} = 0 to 1V, 1V p-p, R_L = 75 Ω		1.3		GHz		
	Off Isolation	V_{IN} = 0 to 1V, 1V p-p, R_L = 75 Ω , f = 5.5MHz	_	-60	_	dB		
X _{TALK}	Crosstalk	$V_{IN} = 1V \text{ p-p}, R_L = 75\Omega,$ f = 5.5MHz		-70	_	dB		
C _(OFF)	MUX Off Capacitance	$\overline{E} = V_{CC}, V_{IN} = V_{OUT} = 0V$		5		pF		
C _(ON)	MUX On Capacitance	$\overline{E} = GND, V_{IN} = V_{OUT} = 0V$		10		pF		
Q _{CI}	Charge Injection	C _L = 1000pF		1.5		рС		

Notes:

- Typical values indicate V_{CC} = 5.0V and T_A = 25°C.
 Guaranteed by design, not subject to production test.
 Measured by voltage drop between A and C or B and D pins at indicated current through the switch. On-resistance is determined by the lower of the voltages on the two (A,C or B,D) pins.
 Δr_{DS(on)} compares on-resistance at the specified V_{IN} Values.
 The bus switch contributes no group delay other than the RC delay of the on-resistance of the switch and load capacitance. Group delay of the bus switch when used in a system is determined by the driving circuit on the capacitance. Group delay of the bus switch, when used in a system, is determined by the driving circuit on the driving side of the switch and its interaction with the load on the driven side.

TYPICAL CHARACTERISTICS





Note: 1. Crosstalk = 20 log $|V_0/V_s|$ 2. Off-isolation = 20 log $|V_0/V_s|$

Figure 4. Off-isolation and Crosstalk vs. Frequency

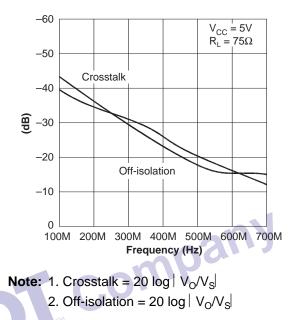
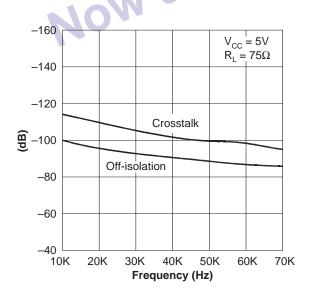


Figure 5. OFF Isolation and Crosstalk vs. Frequency



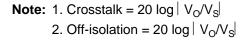
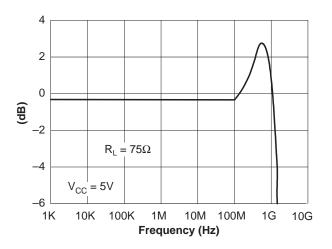


Figure 6. Insertion Loss vs. Frequency

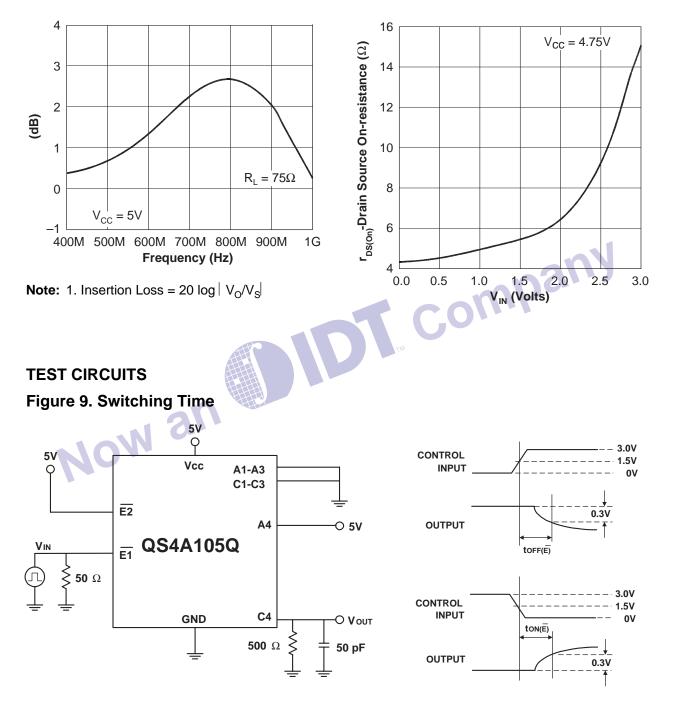


Note: 1. Insertion Loss = $20 \log |V_0/V_s|$

TYPICAL CHARACTERISTICS (continued)



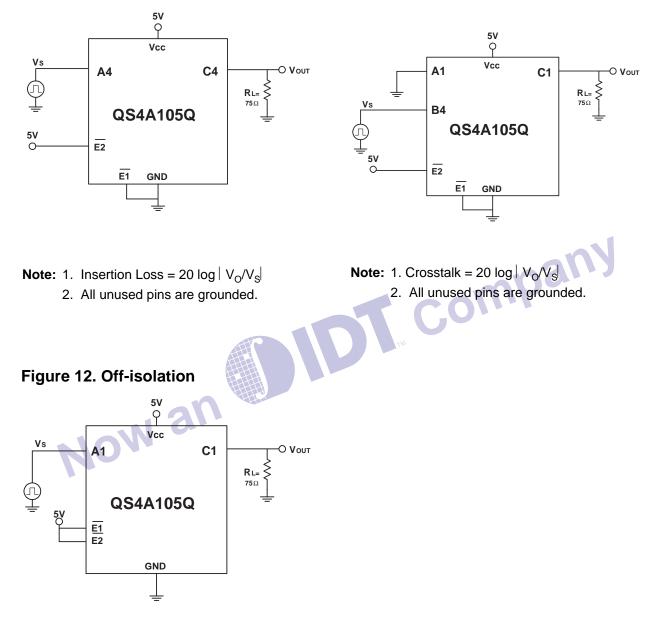
Figure 8. On-resistance vs. V_{IN}



TEST CIRCUITS (continued)



Figure 11. Crosstalk



- **Note:** 1. Off-isolation = $20 \log |V_0/V_s|$
 - 2. All unused pins are grounded.